

IN THE SPECIFICATION

\ Please replace paragraph 0025 with the following rewritten paragraph:

a' -- 0025 Layer 14 may be configured as a layer of aluminum film possessing a thickness in a range of approximately 10KÅ to 20KÅ. Layer 14 thus functions as a buffer and bonding layer, when positioned above single metal layer 12 (i.e. single layer M8 bond pad). Bonding mechanical stresses are illustrated by arrow 22, which also indicates the general direction of an associated wiring bond. Additionally, a plurality of intermetal dielectric (IMD) layers 18 is generally illustrated in FIG. 1 to include IMD1 to IMD7 metal layers. A device 20, such as, for example, an integrated circuit device, may be positioned below layers IMD1 to IMD7 to comprise a device under a single layer bond pad. --

\ Please replace paragraph 0029 with the following rewritten paragraph:

a' -- 0029 FIG. 4 depicts a configuration illustrating thicker aluminum bond pad effects, in accordance with a preferred embodiment of the present invention. All of the associated stresses are generally decreased as the aluminum thickness is increased. Thus, by increasing the aluminum thickness, an enhanced buffer layer can be created to protect the "under" IMD layer from damage that may result from ultrasonic motion. In FIG. 4, a configuration 70 is illustrated indicated a control thickness of 12K resulting from the formation of an aluminum buffer layer 72. Such a layer 72 thus possesses a layer thickness of approximately 12KÅ. A copper wiring bond pad 74 is formed from a single copper metal layer. An aluminum bond pad 76 is also illustrated via configuration 70. Similarly, configuration 71 includes an aluminum bond pad 86 positioned above an aluminum buffer layer 82, which possesses a thickness of approximately 16KÅ. A copper wiring bond pad 84 is also indicated in configuration 71. --